

In the Claims:

Cancel claims 4, 11, 13 and 14.

Amend claim 8 as follows:

8. (Twice Amended) An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,
said first electrode layer including at least one selected from a first metal group consisting of Ti, Hf, Zr, Nb, Ta and Sc,
said second electrode layer comprising, and
said third electrode layer including Au.

Ti / Nb / Au

Add the following new claims 15-18 as follows:

15. An electrode structure on a p-type III group nitride semiconductor layer, comprising first, second and third electrode layers successively stacked on said semiconductor layer,
said first electrode layer including at least one selected from a first metal group consisting of Nb, Ta and Sc,
said second electrode layer including at least one selected from a second metal group consisting of Ni, Pd and Co, and
said third electrode layer including Au.

16. The electrode structure according to claim 15, wherein said first electrode layer has a thickness in a range from 1 to 500 nm.

17. The electrode structure according to claim 15, wherein said second electrode layer has a thickness of 5 nm or more.

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broad

18. The electrode structure of claim 15, wherein said first electrode layer includes a nitride of a metal included in said first metal group, and also includes a compound of Ga and a metal included in said second metal group.
